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4 a plurality of basic cells regularly arranged on said
5 semiconductor substrate;

6 a plurality of field effect transistors arranged in
7 each of a plurality of said basic cells and formed in said
8 semiconductor region;

9 power supply wirings arranged for supplying the power
10 supply voltages to a plurality of said field effect
11 transistors; and

12 switch elements provided between said semiconductor
13 region and said power supply wirings,

14 wherein said switch elements include field effect
15 transistors of said basic cells.

Please cancel Claims 2-6 without prejudice or
disclaimer.

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1 22. (Twice Amended) A semiconductor device as claimed
2 in any one of claims 7 to 12, further comprising:

3 a first wiring layer formed over said switch elements;

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4 a second wiring layer formed over said first wiring
5 layer and having wiring extending in a direction transverse
6 to wiring of said first wiring layer; and

7 a third wiring layer formed over said second wiring

8 layer and having wiring extending in a direction transverse
9 to wiring of said second wiring layer,

10 wherein a wiring electrically connected to gate
11 electrodes of said switch elements is formed of wiring of
12 the third wiring layer and arranged in parallel to said
13 power supply wirings.

1 23. (Twice Amended) A semiconductor device as claimed
2 in any one of claims 7 to 14, wherein a semiconductor
3 region for power feeding to supply a predetermined voltage
4 to the semiconductor region formed in said semiconductor
5 substrate is formed in a region between an internal circuit
6 region where a plurality of said basic cells are arranged
7 and a peripheral circuit region at an external side of said
8 internal circuit region.

1 34. (Amended) A semiconductor device, comprising:
2 a semiconductor region formed in a peripheral circuit
3 region of a semiconductor substrate;
4 a plurality of cells for input/output circuits
5 regularly arranged in the peripheral circuit region of said
6 semiconductor substrate;
7 a plurality of field effect transistors for

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8 input/output circuits arranged in each of a plurality of
9 said cells for input/output circuits and formed in said
10 semiconductor region;
11 power supply wiring arranged for supplying a power
12 supply voltage to a plurality of said field effect
13 transistors for input/output circuits; and
14 switch elements provided between the semiconductor
15 region in said peripheral circuit region and said power
16 supply wiring,
17 wherein said peripheral circuit region includes an
18 external region to arrange field effect transistors for
19 input/output circuits of relatively higher threshold
20 voltage and an internal region to arrange field effect
21 transistors for input/output circuits of relatively lower
22 threshold voltage, and
23 wherein said switch elements include field effect
24 transistors not used for input circuit among the field
25 effect transistors for input/output circuits in said
26 internal region.

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39. (Amended) A method of manufacturing a

2 semiconductor device, comprising:

3 (a) regularly allocating a plurality of basic cells on